TB PACKAGE

400 MIL TAB

CASE 984A-01

MCM101525

Product Preview 2M x 2 Bit Fast Static **Random Access Memory with** ECL I/O

The MCM101525 is a 4,194,304 bit static random access memory organized as 2,097,152 words of 2 bits. This device features complementary outputs. This circuit is fabricated using high performance silicon-gate BiCMOS technology. Asynchronous design eliminates the need for external clocks or timing strobes. The MCM101525 is available in a 400 mil, 36 lead TAB.

- Fast Access Times: 12,
- Equal Address and Chip Select Access Time
- Power Operation: 195 mA Maximum, Active AC



	PIN N	AMES
S	S Chip Select	W Write Enable D0 – D1 Data Input
Q	Q0 – Q1 Data Output	$\overline{Q0}$ and $\overline{Q1}$. Complementary Data Out
N	IC No Connection	VEE Power Supply
V	CC ····· Ground	

This document contains information on a new product under development. Motorola reserves the right to change or discontinue this product without notice.



15 ns





A10 [1 •	36	A1
A11 🛛 :	2	35] A2
A12 🛛 🗄	3	34] A3
A13 🛛 -	4	33	D A8
A14 🛛	5	32	D A19
sΟ	6	31	П NC
D0 [7	30	A20
Q0 [8	29	
V _{CC} [9	28	D V _{EE}
Vee C	10	27	□ v _{cc}
	11	26] Q1
Vee D	12	25	D D1
ѿҨ	13	24	□ мс
ао 🛙	14	23] A9
A15 [15	22	D A4
A16 🛛	16	21] A5
A17 🛛	17	20	D A6
A18 🛛	18	19] A7

BLOCK DIAGRAM

TRUTH TABLE (X = Don't Care)

S	W	Operation	Data	Output	Current
Н	Х	Not Enabled	Х	L	
L	Н	Read	Х	Q/\overline{Q}	IEE
L	L	Write	Х	L	IEE

ABSOLUTE MAXIMUM RATINGS (See Note)

Rating	Symbol	Value	Unit
V _{EE} Pin Potential (to Ground)	VEE	- 7.0 to + 0.5	V
Voltage Relative to V_{CC} for Any Pin Except V_{EE}	V _{in} , V _{out}	$V_{EE} - 0.5 \text{ to} + 0.5$	V
Output Current (per I/O)	lout	- 50	mA
Power Dissipation	PD	2.0	W
Temperature Under Bias	T _{bias}	– 30 to + 85	°C
Operating Temperature	Tj	0 to + 60	°C
Storage Temperature — Plastic	T _{stg}	- 55 to + 125	°C

This device contains circuitry to protect the inputs against damage due to high static voltages or electric fields; however, it is advised that normal precautions be taken to avoid application of any voltage higher than maximum rated voltages to these high impedance circuits.

This BiCMOS memory circuit has been designed to meet the dc and ac specifications shown in the tables, after thermal equilibrium has been established. The circuit is in a test socket or mounted on a printed circuit board and transverse air flow of at least 500 linear feet per minute is maintained.

NOTE: Permanent device damage may occur if ABSOLUTE MAXIMUM RATINGS are exceeded. Functional operation should be restricted to the OPERATING CONDI-TIONS. Exposure to higher than recommended voltages for extended periods of time could affect device reliability.

DC OPERATING CONDITIONS AND CHARACTERISTICS

 $(V_{CC} = 0 \text{ V}, \text{ V}_{EE} = -5.2 \text{ V} \pm 5\%, \text{ T}_{J} = 0 \text{ to } + 60^{\circ}\text{C}, \text{ Unless Otherwise Noted})$

DC OPERATING CONDITIONS AND SUPPLY CURRENTS

Parameter	Symbol	Min	Тур	Max	Unit	
Supply Voltage (Operating Voltage Range)	VEE	- 5.46	- 5.2	- 4.94	V	
Input High Voltage	VIH	- 1165	—	- 880	mV	
Input Low Voltage	VIL	- 1810	—	- 1475	mV	
Output High Voltage	VOH	- 1025	—	- 880	mV	
Output Low Voltage	V _{OL}	- 1810	—	- 1620	mV	
Input Low Current	١ _{IL}	- 50	—	—	μΑ	
Input High Current	Ιн	—	—	220	μΑ	
Chip Select Input Low Current	IIL(CS)	0.5	—	170	μΑ	
Operating Power Supply Current: ^t AVAV = 20 ns (All Outputs Open)*	IEE	—	—	- 195	mA	
Quiescent Power Supply Current: f ₀ = 0 MHz (Outputs Open)	IEEQ	—	—	- 150	mA	
Voltage Compensation (V _{OH})	$\Delta V_{OH} / \Delta V_{EE}$	± 35	±35 mV/V @ -4.94 to -5.46 V			
Voltage Compensation (V _{OL})	$\Delta V_{OL} / \Delta V_{EE}$	± 60	mV/V @ – 4.9	94 to – 5.46 V	,	

* Address Increment

RISE/FALL TIME CHARACTERISTICS

Parameter	Symbol	Test Condition	Min	Тур	Max	Unit
Output Rise Time	tr	20% to 80%	0.5	1.0	1.5	ns
Output Fall Time	t _f	20% to 80%	0.5	1.0	1.5	ns

CAPACITANCE (f = 1.0 MHz, T_A = 25°C, Periodically Sampled Rather Than 100% Tested)

Parameter	Symbol	Тур	Max	Unit
Input Capacitance Address and Data $\overline{S}, \overline{W}$	C _{in} C _{ck}	3.5 4	7 7	pF
Output Capacitance \$\overline{Q}\$, Q	Cout	4	8	pF

AC OPERATING CONDITIONS AND CHARACTERISTICS

(VEE = $-5.2 \text{ V} \pm 5\%$, V_{CC} = 0 V, T_J = 0 to +60°C, Unless Otherwise Noted)

Input Pulse Levels	- 1.7 V to - 0.9 V (See Figure 1)
Input Rise/Fall Time	1 ns	s
Input Timing Measurement Refere	nce Level 50%	6

READ CYCLE TIMING (See Notes 1 and 2)

		MCM10 ²	1525–12	MCM10 ²	1525–15		
Parameter	Symbol	Min	Max	Min	Max	Unit	Notes
Read Cycle Time	^t AVAV	12	—	15	-	ns	2, 3
Address Access Time	^t AVQV	—	12	—	15	ns	
Chip Select Access Time	^t SLQV	—	12	—	15	ns	6
Select High to Output Low	^t SHQL	0	8	0	9	ns	
Output Hold from Address Change	t _{AXQX}	4	—	4	—	ns	
Power Up Time	^t SLIEEH	0	—	0	_	ns	4
Power Down Time	^t SHIEEL	_	12	—	15	ns	4

NOTES:

1. \overline{W} is high for read cycle.

2. Product sensitivites to noise require proper grounding and decoupling of power supplies during read and write cycles.

3. All read cycle timings are referenced from the last valid address to the first transitioning address.

4. This parameter is sampled and not 100% tested.

5. Device is continuously selected ($\overline{S} \leq V_{IL}$).

6. Addresses valid prior to or coincident with \overline{S} going low.

AC TEST CONDITIONS



 t_{Γ} = Rise Time t_{f} = Fall Time 50% = Timing Reference Levels





Figure 2. AC Test Circuit

READ CYCLE 1 (See Notes 1, 2, and 5)



WRITE CYCLE 1 (W Controlled, See Notes 1 and 2)

		MCM101525–12 MCM101525–1		MCM101525-15			
Parameter	Symbol	Min	Max	Min	Max	Unit	Notes
Write Cycle Time	t _{AVAV}	12	—	15	_	ns	3
Address Setup Time	^t AVWL	1	—	1	_	ns	
Address Valid to End of Write	^t AVWH	9	—	10	_	ns	
Write Pulse Width	^t WLWH [,] ^t WLSH	8	—	9	_	ns	
Data Valid to End of Write	^t DVWH	8	—	9	_	ns	
Data Hold Time	tWHDX	1	—	1	_	ns	
Write High to Output Active	tWHQX	4	-	4	_	ns	4
Write High to Output Valid	^t WHQV	—	13	—	16	ns	
Write Recovery Time	tWHAX	1	—	1		ns	
Write Low to Output Low	^t WLQL	0	8	0	9	ns	

NOTES:

1. A write occurs during the overlap of \overline{S} low and \overline{W} low.

2. Product sensitivites to noise require proper grounding and decoupling of power supplies during read and write cycles.

3. All write cycle timings are referenced from the last valid address to the first transitioning address.

4. This parameter is sampled and not 100% tested.



WRITE CYCLE 1 (W Controlled, See Notes 1, 2, and 3)

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WRITE CYCLE 2 (\overline{S} Controlled, See Notes 1 and 2)

		MCM10	1525–12	MCM10	1525–15		
Parameter	Symbol	Min	Max	Min	Max	Unit	Notes
Write Cycle Time	^t AVAV	12	—	15	_	ns	3
Address Setup Time	^t AVSL	1	—	1	—	ns	
Address Valid to End of Write	^t AVSH	9	-	10	—	ns	
	^t SLSH ^t SLWH	8	-	9	—	ns	
Data Valid to End of Write	^t DVSH	8	-	9	—	ns	
Chip Select Set–Up Time	^t SLWL	0	—	0	—	ns	
Data Hold Time	^t SHDX	1	-	1	—	ns	
Write Recovery Time	^t SHAX	1	_	1		ns	

NOTES:

1. A write occurs during the overlap of \overline{S} low and \overline{W} low.

2. Product sensitivites to noise require proper grounding and decoupling of power supplies during read and write cycles.

3. All write cycle timings are referenced from the last valid address to the first transitioning address.



WRITE CYCLE 2 (S Controlled, See Notes 1 and 2)

PACKAGE DIMENSIONS

TB PACKAGE 400 MIL TAB CASE 984A-01



TB PACKAGE 400 MIL TAB CASE 984A–01 (cont.)





BOTTOM VIEW

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